ABSOLUTE MAXIMUM RATINGS

(All voltages are referenced to V _{FE} , unless otherwise noted.)	GND, RCLASS to V _{FF}	70mA
GND (MAX5940A/MAX5940B)0.3V to +80V	UVLO, PGOOD, PGOOD to VEE	20mA
GND (MAX5940C/MAX5940D)0.3V to +90V	GATE to VEE	80mA
OUT, PGOOD0.3V to (GND + 0.3V)	Continuous Power Dissipation ($T_A = +70$ °C)	
RCLASS, GATE0.3V to +12V	8-Pin SO (derate 5.9mW/°C above +70°C)	470mW
UVLO0.3V to +8V	Operating Temperature Range40°C	to +85°C
PGOOD to OUT0.3V to (GND + 0.3V)	Storage Temperature Range65°C to	+150°C
Maximum Input/Output Current (continuous)	Junction Temperature	+150°C
OUT to VEE500mA	Lead Temperature (soldering, 10s)	+300°C
001 to VEE00011// (Load Temperature (soldering, 103)	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{IN} = (GND - V_{EE}) = 48V, GATE = \overline{PGOOD} = PGOOD = OUT = OPEN, UVLO = V_{EE}, T_A = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$. All voltages are referenced to V_{EE} , unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
DETECTION MODE				•			
Input Offset Current (Note 2)	IOFFSET	V _{IN} = 1.4V to 10.1V				10	μΑ
Effective Differential Input Resistance (Note 3)	dR	$V_{IN} = 1.4V \text{ up to}$ $OUT = \overline{PGOOD}$	o 10.1V with 1V step, 5 = GND	550			kΩ
CLASSIFICATION MODE							
Classification Current Turn-Off Threshold (Note 4)	V _{TH,CLSS}	V _{IN} rising		20.8	21.8	22.5	V
			Class 0, $R_{CL} = 10k\Omega$	0		2	
		$V_{IN} = 12.6V \text{ to}$	Class 1, $R_{CL} = 732\Omega$	9.17		11.83	mA
Classification Current (Notes 5, 6)	ICLASS	20V, R _{DISC} =	Class 2, $R_{CL} = 392\Omega$	17.29		19.71	
		25.5kΩ	Class 3, $R_{CL} = 255\Omega$	26.45		29.55	
			Class 4, $R_{CL} = 178\Omega$	36.6		41.4	
POWER MODE							
Operating Supply Voltage	V _{IN}	V _{IN} = (GND - V _{EE})				67	V
Operating Supply Current	I _{IN}	Measure at GND, not including RDISC			0.4	1	mA
			MAX5940A/MAX5940C	34.3	35.4	36.6	
Default Power Turn-On Voltage	V _U VLO, ON	V _{IN} increasing	MAX5940B/MAX5940D, UVLO = V _{EE}	37.4	38.6	39.9	V
Default Power Turn-Off Voltage	Vuvlo, off	V _{IN} decreasing, UVLO = V _{EE} for MAX5940B/MAX5940D		30			V
Default Power Turn-On/Off	V _{HYST} ,	MAX5940A/MAX5940C		4.2			V
Hysteresis	UVLO	MAX5940B/MAX5940D, UVLO = VEE		7.4			7
External UVLO Programming Range	V _{IN,EX}	Set UVLO externally (MAX5940B/ MAX5940D only) (Note 7)		12		67	V
UVLO External Reference Voltage	V _{REF} , UVLO			2.400	2.460	2.522	V
UVLO External Reference Voltage Hysteresis	HYST	Ratio to V _{REF} ,uvLO		19.2	20	20.9	%
UVLO Bias Current	luvlo	UVLO = 2.460V		-1.5		+1.5	μΑ

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = (GND - V_{EE}) = 48V, GATE = \overline{PGOOD} = PGOOD = OUT = OPEN, UVLO = V_{EE}, T_A = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$. All voltages are referenced to V_{EE} , unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
UVLO Input Ground Sense Threshold (Note 8)	V _{TH} ,G,UVLO			50		440	mV
UVLO Input Ground Sense Glitch Rejection		UVLO = VEE			7		μs
Power Turn-Off Voltage, Undervoltage Lockout Deglitch Time (Note 9)	toff_dly	V _{IN} , V _{UVLO} falling		0.32			ms
Isolation Switch N-Channel	Davi	Output current = 300mA, V _{GATE} = 6V, measured between OUT and V _{EE}	$T_A = +25^{\circ}C$ (Note 10)		0.6	1.1	Ω
MOSFET On-Resistance	Ron		T _A = +85°C		0.8	1.5	
Isolation Switch N-Channel MOSFET Off-Threshold Voltage	V _{GSTH}	OUT = GND, V _{GATE} - V _{EE} , output current < 1µA		0.5			V
GATE Pulldown Switch Resistance	RG	Power-off mode, V _{IN} = 12V, UVLO = V _{EE} for MAX5940B			38	80	Ω
GATE Charging Current	IG	VGATE = 2V		5	10	15	μΑ
GATE High Voltage	VGATE	IGATE = 1µA		5.59	5.76	5.93	V
PGOOD, PGOOD Assertion V _{OUT}	Vouten	V _{OUT} - V _{EE} , IV _{OUT} - V _{EE} I decreasing, V _{GATE} = 5.75V		1.16	1.23	1.31	٧
Threshold		Hysteresis			70		mV
PGOOD, PGOOD Assertion VGATE	VGSEN	(GATE - V _{EE}) increasir	ng, OUT = VEE	4.62	4.76	4.91	V
Threshold		Hysteresis			80		mV
PGOOD, PGOOD Output Low Voltage (Note 11)	Voldcdc	I _{SINK} = 2mA; for PGOOD, OUT ≤ (GND - 5V)				0.4	V
PGOOD Leakage Current (Note 11)		GATE = high, GND - V _{OUT} = 67V				1	μΑ
PGOOD Leakage Current (Note 11)		$GATE = V_{EE}, \overline{PGOOD}$	- V _{EE} = 67V			1	μΑ

- Note 1: All min/max limits are production tested at +85°C. Limits at +25°C and -40°C are guaranteed by design.
- Note 2: The input offset current is illustrated in Figure 1.
- **Note 3:** Effective differential input resistance is defined as the differential resistance between GND and V_{EE} without any external resistance. See Figure 1.
- Note 4: Classification current is turned off whenever the IC is in power mode.
- Note 5: See Table 2 in the PD Classification Mode section. RDISC and RCL must be ±1%, 100ppm or better. ICLASS includes the IC bias current and the current drawn by RDISC.
- Note 6: See the *Thermal Dissipation* section for details.
- Note 7: When UVLO is connected to the midpoint of an external resistor-divider with a series resistance of 25.5k Ω (\pm 1%), the turn-on threshold set-point for the power mode is defined by the external resistor-divider. Make sure the voltage on the UVLO pin does not exceed its maximum rating of 8V when V_{IN} is at the maximum voltage (MAX5940B only).
- Note 8: When the UVLO input voltage is below V_{TH,G,UVLO}, the MAX5940B sets the UVLO threshold internally.
- Note 9: An input voltage or V_{UVLO} glitch below their respective thresholds shorter than or equal to t_{OFF_DLY} does not cause the MAX5940A/MAX5940B/MAX5940C/MAX5940D to exit power-on mode (as long as the input voltage remains above an operable voltage level of 12V).
- Note 10: Guaranteed by design.
- Note 11: PGOOD references to OUT while PGOOD references to VFF.

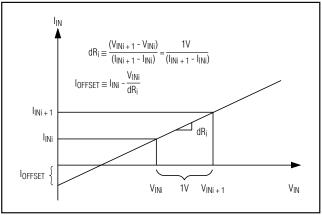
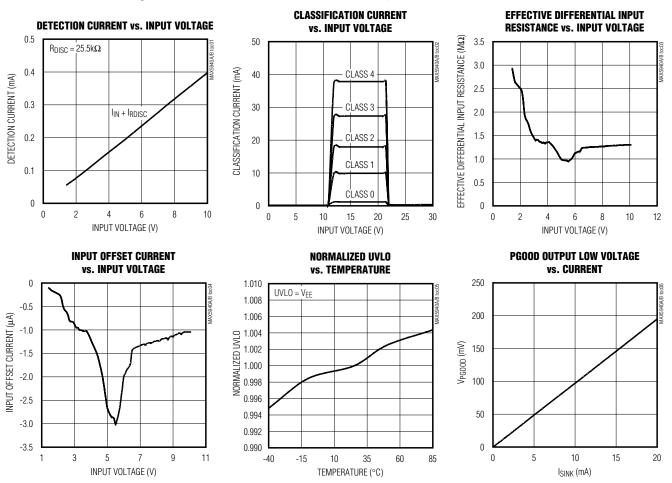


Figure 1. Effective Differential Input Resistance/Offset Current

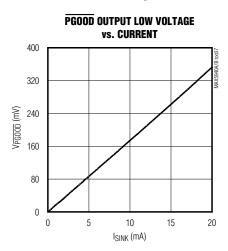
_Typical Operating Characteristics

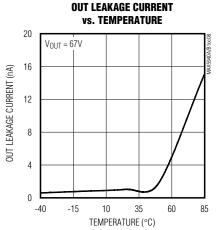
 $(V_{IN} = (GND - V_{EE}) = 48V, GATE = \overline{PGOOD} = PGOOD = OUT = OPEN, UVLO = V_{EE} (MAX5940B), T_A = -40^{\circ}C to +85^{\circ}C.$ Typical values are at $T_A = +25^{\circ}C.$ All voltages are referenced to V_{EE} , unless otherwise noted.)

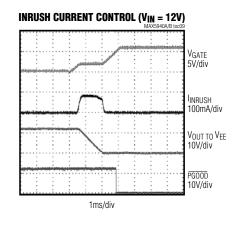


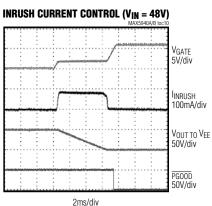
Typical Operating Characteristics (continued)

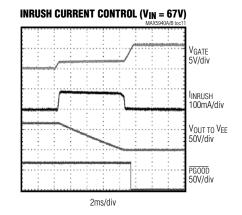
 $(V_{IN} = (GND - V_{EE}) = 48V, \ GATE = \overline{PGOOD} = PGOOD = OUT = OPEN, \ UVLO = V_{EE} \ (MAX5940B), \ T_A = -40^{\circ}C \ to \ +85^{\circ}C. \ Typical \ values are at \ T_A = +25^{\circ}C. \ All \ voltages \ are \ referenced \ to \ V_{EE}, \ unless \ otherwise \ noted.)$











Pin Description

PIN MAX5940A/ MAX5940B/ MAX5940C MAX5940D			
		NAME	FUNCTION
1, 7	_	N.C.	No Connection. Not internally connected.
_	1	UVLO	Undervoltage Lockout Programming Input for Power Mode. When UVLO is above its threshold, the device enters power mode. Connect UVLO to VEE to use the default undervoltage lockout threshold. Connect UVLO to an external resistor-divider to define a threshold externally. The series resistance value of the external resistors must add to 25.5k Ω (±1%) and replaces the detection resistor. To keep the device in undervoltage lockout, pull UVLO to between VTH,G,UVLO and VREF,UVLO.
2	2	RCLASS	Classification Setting. Add a resistor from RCLASS to VEE to set a PD class (see Tables 1 and 2).
3	3	GATE	Gate of Internal N-Channel Power MOSFET. GATE sources 10µA when the device enters power mode. Connect an external 100V ceramic capacitor (C _{GATE}) from GATE to OUT to program the inrush current. Pull GATE to V _{EE} to turn off the internal MOSFET. The detection and classification functions operate normally when GATE is pulled to V _{EE} .
4	4	VEE	Negative Input Power. Source of the integrated isolation N-channel power MOSFET. Connect VEE to -48V.
5	5	OUT	Output Voltage. Drain of the integrated isolation N-channel power MOSFET.
6	6	PGOOD	Power-Good Indicator Output, Active-High, Open-Drain. PGOOD is referenced to OUT. PGOOD goes high impedance when V _{OUT} is within 1.2V of V _{EE} and when GATE is 5V above V _{EE} . Otherwise, PGOOD is pulled to OUT (given that V _{OUT} is at least 5V below GND). Connect PGOOD to the ON pin of a downstream DC-DC converter.
_	7	PGOOD	Power-Good Indicator Output, Active-Low, Open-Drain. PGOOD is referenced to VEE. PGOOD is pulled to VEE when VOUT is within 1.2V of VEE and when GATE is 5V above VEE. Otherwise, PGOOD goes high impedance. Connect PGOOD to the ON pin of a downstream DC-DC converter.
8	8	GND	Ground. GND is the positive input terminal.

Detailed Description

Operating Modes

The PD front-end section of the MAX5940_ operates in 3 different modes, PD detection signature, PD classification, and PD power, depending on its input voltage ($V_{IN} = GND - V_{EE}$). All voltage thresholds are designed to operate with or without the optional diode bridge while still complying with the IEEE 802.3af standard (see Figure 4).

Detection Mode (1.4 $V \le V_{IN} \le 10.1V$)

In detection mode, the power source equipment (PSE) applies two voltages on V_{IN} in the range of 1.4V to 10.1V

(1V step minimum), and then records the current measurements at the two points. The PSE then computes $\Delta V/\Delta I$ to ensure the presence of the 25.5k Ω signature resistor. In this mode, most of the MAX5940_ internal circuitry is off and the offset current is less than 10 μ A.

If the voltage applied to the PD is reversed, install protection diodes on the input terminal to prevent internal damage to the MAX5940_ (see the Typical Application Circuits). Since the PSE uses a slope technique ($\Delta V/\Delta I$) to calculate the signature resistance, the DC offset due to the protection diodes is subtracted and does not affect the detection process.

__ /N/1XI/N

Table 1. PD Power Classification/RCL Selection

CLASS	USAGE	R _{CL} (Ω)	MAXIMUM POWER USED BY PD (W)
0	Default	10k	0.44 to 12.95
1	Optional	732	0.44 to 3.84
2	Optional	392	3.84 to 6.49
3	Optional	255	6.49 to 12.95
4	Not Allowed	178	Reserved*

^{*}Class 4 reserved for future use.

Table 2. Setting Classification Current

CLASS	R _{CL} (Ω)	V _{IN} * (V)	CLASS CURRENT	SEEN AT V _{IN} (mA)	IEEE 802.3af PD CLASSIFICATION CURRENT SPECIFICATION (mA)		
			MIN	MAX	MIN	MAX	
0	10k	12.6 to 20	0	2	0	4	
1	732	12.6 to 20	9.17	11.83	9	12	
2	392	12.6 to 20	17.29	19.71	17	20	
3	255	12.6 to 20	26.45	29.55	26	30	
4	178	12.6 to 20	36.6	41.4	36	44	

 $^{^*}$ V_{IN} is measured across the MAX5940 input pins, which does not include the diode bridge voltage drop.

Classification Mode (12.6 $V \le V_{IN} \le 20V$)

In the classification mode, the PSE classifies the PD based on the power consumption required by the PD. This allows the PSE to efficiently manage power distribution. The IEEE 802.3af standard defines five different classes as shown in Table 1. An external resistor (RCL) connected from RCLASS to VEE sets the classification current.

The PSE determines the class of a PD by applying a voltage at the PD input and measures the current sourced out of the PSE. When the PSE applies a voltage between 12.6V and 20V, the MAX5940_ exhibit a current characteristic with values indicated in Table 2. The PSE uses the classification current information to classify the power requirement of the PD. The classification current includes the current drawn by the 25.5k Ω detection signature resistor and the supply current of the MAX5940_ so the total current drawn by the PD is within the IEEE 802.3af standard figures. The classification current is turned off whenever the device is in power mode.

Power Mode

During power mode, when V_{IN} rises above the undervoltage lockout threshold ($V_{UVLO,ON}$), the MAX5940_gradually turn on the internal N-channel MOSFET Q1

(see Figure 2). The MAX5940_ charge the gate of Q1 with a constant current source (10µA, typ). The drainto-gate capacitance of Q1 limits the voltage rise rate at the drain of the MOSFET, thereby limiting the inrush current. To reduce the inrush current, add external drain-to-gate capacitance (see the *Inrush Current Limit* section). When the drain of Q1 is within 1.2V of its source voltage and its gate-to-source voltage is above 5V, the MAX5940_ asserts the PGOOD/PGOOD outputs. The MAX5940_ have a wide UVLO hysteresis and turn-off deglitch time to compensate for the high impedance of the twisted-pair cable.

Undervoltage Lockout

The MAX5940_ operate up to a 67V supply voltage with a default UVLO turn-on (VUVLO,ON) set at 35V (MAX5940A/MAX5940C) or 39V (MAX5940B/MAX5940D) and a UVLO turn-off (VUVLO,OFF) set at 30V. The MAX5940B/MAX5940D have an adjustable UVLO threshold using a resistor-divider connected to UVLO (see Figure 3). When the input voltage is above the UVLO threshold, the IC is in power mode and the MOSFET is on. When the input voltage goes below the UVLO threshold for more than toff DLY, the MOSFET turns off.

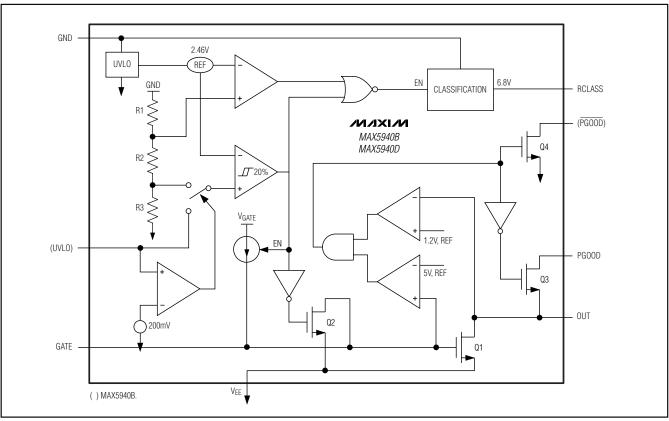


Figure 2. Block Diagram

To adjust the UVLO threshold (MAX5940B/MAX5940D only), connect an external resistor-divider from GND to UVLO and from UVLO to VEE. Use the following equations to calculate R1 and R2 for a desired UVLO threshold:

$$R2 = 25.5k\Omega \times \frac{V_{REF,UVLO}}{V_{IN,EX}}$$

$$R1 = 25.5k\Omega - R2$$

where V_{IN,EX} is the desired UVLO threshold. Since the resistor-divider replaces the $25.5 k\Omega$ PD detection resistor, ensure that the sum of R1 and R2 equals $25.5 k\Omega$ $\pm 1\%$. When using the external resistor-divider, the MAX5940B/MAX5940D has an external reference voltage hysteresis of 20% (typ). When UVLO is programmed externally, the turn-off threshold is 80% (typ) of the new UVLO threshold.

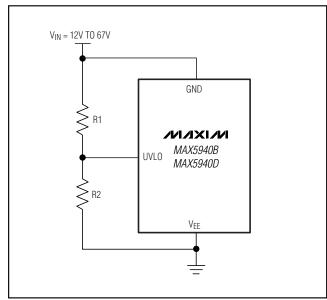


Figure 3. Setting Undervoltage Lockout with an External Resistor-Divider

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Inrush Current Limit

The MAX5940_ charge the gate of the internal MOSFET with a constant current source (10µA, typ). The drainto-gate capacitance of the MOSFET limits the voltage rise rate at the drain, thereby limiting the inrush current. Add an external capacitor from GATE to OUT to further reduce the inrush current. Use the following equation to calculate the inrush current:

$$I_{INRUSH} = I_G \times \frac{C_{OUT}}{C_{GATE}}$$

PGOOD/PGOOD Outputs (MAX5940A/MAX5940C only)

PGOOD is an open-drain, active-high logic output. PGOOD goes high impedance when V_{OUT} is within 1.2V of V_{EE} and when GATE is 5V above V_{EE}. Otherwise, PGOOD is pulled to V_{OUT} (given that V_{OUT} is at least 5V below GND). Connect PGOOD to the ON pin of a downstream DC-DC converter. Connect a $100 \text{k}\Omega$ pullup resistor from PGOOD to GND if needed.

(MAX5940B/MAX5940D only)

 \overline{PGOOD} is an open-drain, active-low logic output. \overline{PGOOD} is pulled to VEE when VOUT is within 1.2V of VEE and when GATE is 5V above VEE. Otherwise, \overline{PGOOD} goes high impedance. Connect \overline{PGOOD} to the \overline{ON} pin of a downstream DC-DC converter. Connect a 100kΩ pullup resistor from \overline{PGOOD} to GND if needed.

Thermal Dissipation

During classification mode, if the PSE applies the maximum DC voltage, the maximum voltage drop from GND to VRCLASS will be 13V. If the maximum classification current of 42mA flows through the MAX5940_, then the maximum DC power dissipation will be 546mW, which is slightly higher than the maximum DC power dissipation of the IC at maximum operating temperature. However, according to the IEEE 802.3af standard, the duration of the classification mode is limited to 75ms (max). The MAX5940_ handle the maximum classification power dissipation for the maximum duration time without sustaining any internal damage. If the PSE violates the IEEE 802.3af standard by exceeding the 75ms maximum classification duration, it may cause internal damage to the IC.



Typical Application Circuits

Application Circuit 1

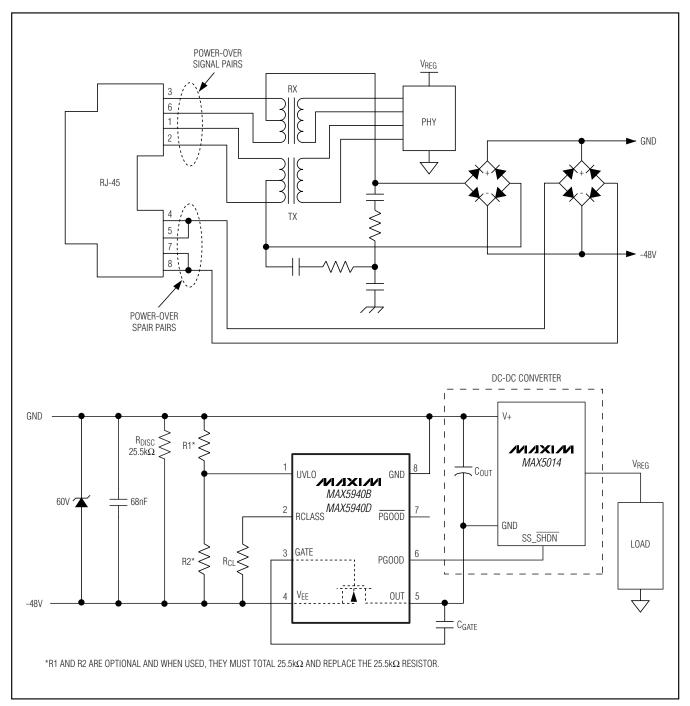


Figure 4. PD with Power-Over-Ethernet (Power is Provided by Either the Signal Pairs or the Spare Pairs)

10 ______ 10 _____ 10 ____ 10 ____ 10 ____ 10 ____ 10 ____ 10 ____ 10 ___ 10 ___

Typical Application Circuits (continued)

Application Circuit 2

Diode D1 prevents the power-over-ethernet to back drive the wall adapter. Whenever the wall adapter power is greater than (V_{D3} + approximately 2V), the

GATE is pulled low to pinch off the power-over-ethernet. The wall adapter power pollutes the discovery signature, preventing PSE from detecting this PD.

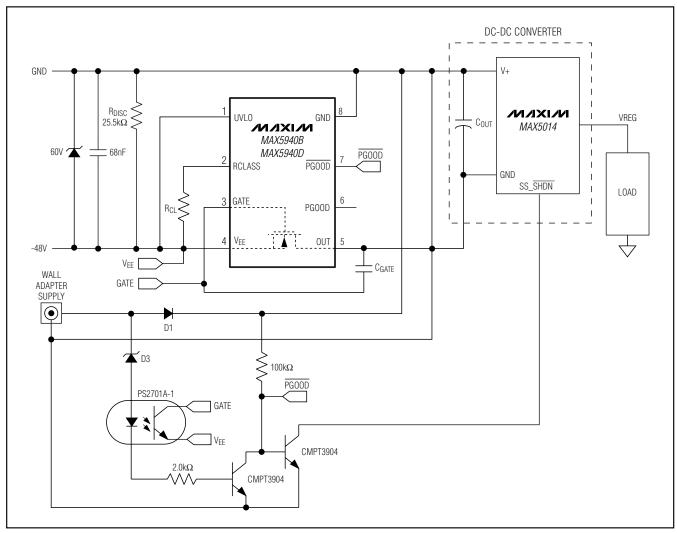


Figure 5. Adding Wall Adapter Input Supply (Wall Adapter Supply Takes Precedence Over Power-Over-Ethernet)

Typical Application Circuits (continued)

Application Circuit 3

D2 prevents the wall adapter power from polluting the discovery and classification signatures. The optional

R4 provides the 10mA minimum power maintenance signature to keep the power-over-ethernet from disconnecting.

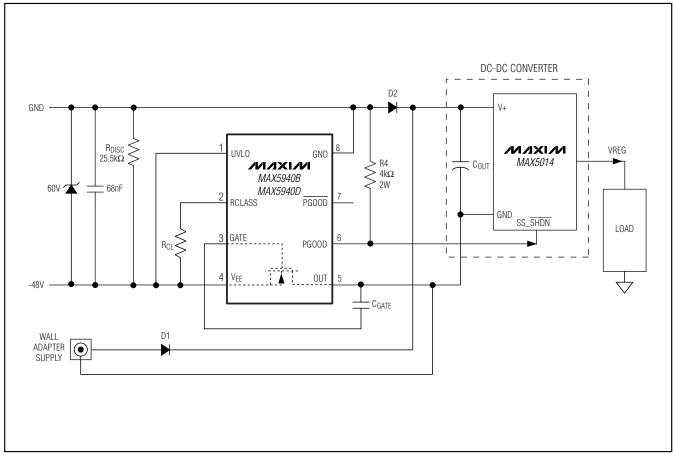


Figure 6. Adding Wall Adapter Input Supply (Wall Adapter Supply And Power-Over-Ethernet Co-Exist, the One with Higher Voltage Provides Power To The Load)

Typical Application Circuits (continued)

Application Circuit 4

If the wall adapter supply comes up first, it provides power to the load and pollute the discovery and classification signatures. If the power-over-ethernet comes up first, it powers the load until taken over by a wall adapter with higher output voltage.

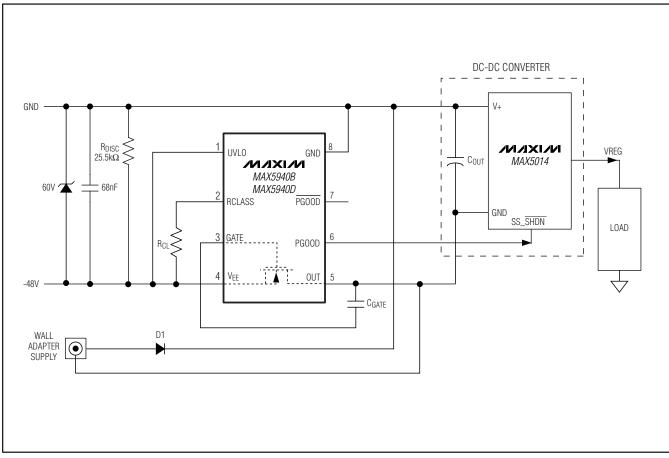
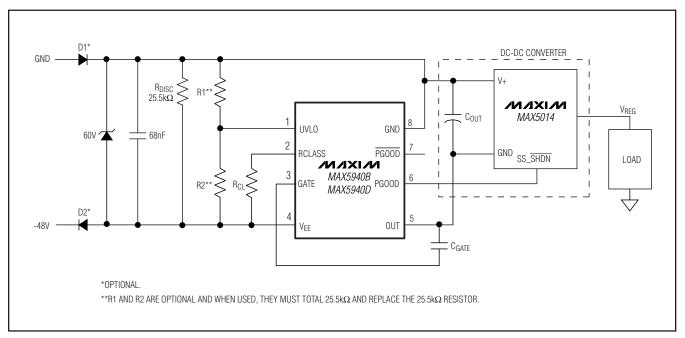


Figure 7. Adding Wall Adapter Input Supply (the One with Higher Voltage Provides Power to the Load)

Typical Operating Circuits (continued)



Pin Configurations

TOP VIEW N.C. 1 8 GND MIXIM RCLASS 2 7 N.C. MAX5940A GATE 3 MAX5940C 6 PGOOD 5 OUT V_{EE} 4 SO UVLO 1 8 GND MIXIM RCLASS 2 7 PGOOD MAX5940B MAX5940D GATE 3 6 PGOOD 5 OUT V_{EE} 4 so

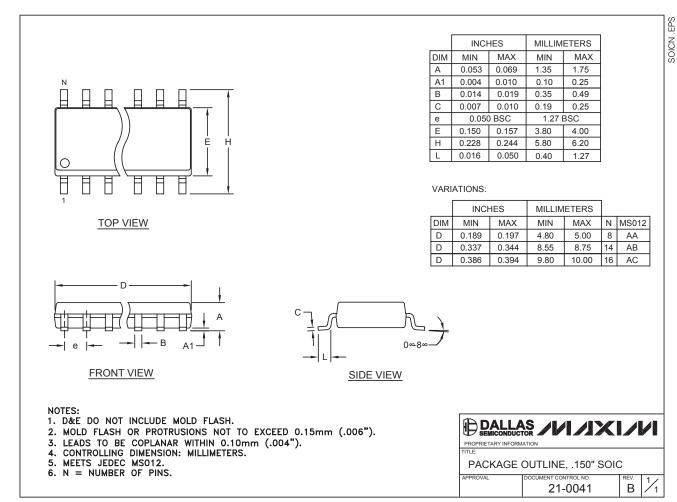
_Chip Information

TRANSISTOR COUNT: 3,643 PROCESS: BICMOS

M/IXI/N

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



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